

## LIST OF PUBLICATIONS

- 1) K.Kaewyai, S. Choopun, M. Thepnurat, A.Gardchareon, S. Phadunghitidhada, , and D.Wongratanaphisan, “Preparation and characterization of copper oxide nanofibers by microwave-assisted thermal oxidation”, Journal of Nanoelectronics and Optoelectronics 8 (2013) 472- 476. (IF = 0.4)
- 2) K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadungdhitidhada, and D. Wongratanaphisana, “Effects of mixed-phase copper oxide nanofibers in ZnO dye-sensitized solar cells on efficiency enhancement” , Journal of Nanoscience and Nanotechnology, Accepted status . (IF =1.33)
- 3) K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadungdhitidhada, and D. Wongratanaphisana, “CuO-Cu<sub>2</sub>O nanocomposite layer for light-harvesting enhancement in ZnO dye-sensitized solar cells”, Submitted to Materials Chemistry and Physics.
- 4) K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadungdhitidhada, and D. Wongratanaphisana, “Mechanism and experimental evidence of rapid morphological variant of copper oxide nanostructures by microwave heating”, Submitted to Nanoscale.
- 5) Karakade Kaewyai, Atcharawon Gardchareon, Supab Choopun , Suurachet Phadunghitidhada, Meechai Thepnurat and Duangmanee Wongratanaphisan, “Preparation of Nanocopper Oxides by Microwave and Characterization”, Proceeding of Collaborative Conference on 3D & Materials Research (2013).
- 6) Karakade Kaewyai, Supab Choopun, Atcharawon Gardchareon, Surachet Phadunghitidhada,and DuangmaneeWongratanaphisan, “Synthesis and Characterization of Copper Oxide Nanofibers”, Proceeding of International Conference on Nano/Molecular Medicine and Engineering (2013).

- 7) K. Kaewyai, A. Gardchareon, S. Choopun, S. Phadunhitidhada, P. Ruankham and D. Wongratanaphisan, “Screening copper oxide nanofibers as a barrier in ZnO dye-sensitized solar cells for efficiency enhancement” Proceeding of Eighth International Conference on Molecular Electronics and Bioelectronics (2015).

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## APPENDIX A

### Characterizations of Copper Oxide Nanostructures Nanostructures

#### 1. The TEM Analysis of Copper Oxide Nanoparticles by Camera-Constant Method

##### 1.1 CuO nanoparticles

This method uses the camera constant ( $L\lambda$ ) and diffraction pattern of the nanoparticle in spot pattern to identify the type and the structure of single crystal. The analysis is as follows:

- Measure the distance from a chosen spot (or spot center) to the 4 closer spots as shown in Figure A.1.
- Calculate  $d_{hkl}$  by using:

$$d_{hkl} = \frac{L\lambda}{r} \quad (\text{A.1})$$

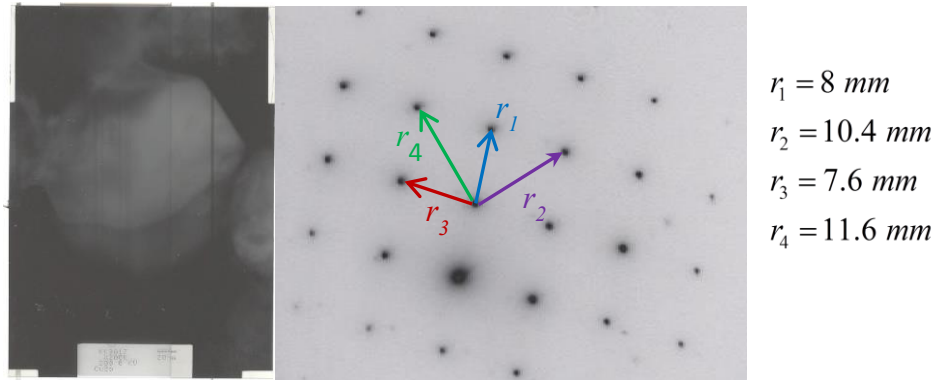
where  $d_{hkl}$  is the d-spacing,  $L\lambda$  is the camera constant (20.2530 mmÅ) and  $r$  is the vector from measured distance. Thus,

$$d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm}\overset{\circ}{\text{Å}}}{8 \text{ mm}} = 2.5316 \overset{\circ}{\text{Å}}$$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm}\overset{\circ}{\text{Å}}}{10.4 \text{ mm}} = 1.9474 \overset{\circ}{\text{Å}}$$

$$d_3 = \frac{L\lambda}{r_3} = \frac{20.2530 \text{ mm}\overset{\circ}{\text{Å}}}{7.6 \text{ mm}} = 2.6648 \overset{\circ}{\text{Å}}$$

$$d_4 = \frac{L\lambda}{r_4} = \frac{20.2530 \text{ mm}\overset{\circ}{\text{Å}}}{11.6 \text{ mm}} = 1.7459 \overset{\circ}{\text{Å}}$$



(a) (b)

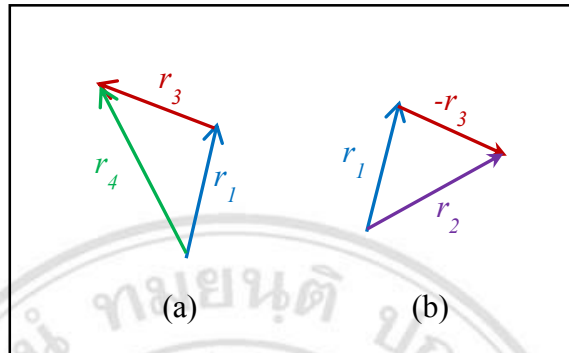
**Figure A.1** (a) TEM image of a copper oxide nanoparticle and (b) the diffraction pattern of the nanoparticle with  $r$ .

- To compare  $d_1, d_2, d_3$ , and  $d_4$  to  $d_{hkl}$  in the data base, this is shown in Figure A.2. From the data base,  $d_1, d_2, d_3$  and  $d_4$  are a plane of 002,  $1\bar{1}2$ ,  $\bar{1}10$  and  $\bar{1}12$ , respectively.

dhkl	(hkl)	Sind?	Teta	Fs?	P	I%
5.058	(001)	1	8.76	4.00	2	100
4.619	(100)	1	9.60	0.00	2	0
3.733	(-101)	2	11.91	0.00	2	0
3.427	(010)	1	12.99	0.00	2	0
3.160	(101)	2	14.11	0.00	2	0
2.837	(0-11)	2	15.76	0.00	4	0
	(011)	2	15.76	0.00	4	0
2.752	(-110)	2	16.25	4.00	4	55
	(110)	2	16.25	4.00	4	55
2.529	(002)	4	17.73	4.00	2	23
2.524	(-111)	3	17.77	4.00	4	45
	(11-1)	3	17.77	4.00	4	45
2.391	(-102)	5	18.79	0.00	2	0
2.323	(1-11)	3	19.37	4.00	4	37
	(111)	3	19.37	4.00	4	37
2.309	(200)	4	19.48	4.00	2	18
2.246	(20-1)	5	20.06	4.00	2	17
2.078	(102)	5	21.76	0.00	2	0
2.035	(012)	5	22.24	0.00	4	0
	(0-12)	5	22.24	0.00	4	0
1.980	(201)	5	22.89	4.00	2	13
1.961	(-1-12)	6	23.13	4.00	4	25
	(-112)	6	23.13	4.00	4	25
1.915	(2-10)	5	23.72	0.00	4	0
	(210)	5	23.72	0.00	4	0
1.879	(-211)	6	24.21	0.00	4	0
	(21-1)	6	24.21	0.00	4	0
1.866	(-202)	8	24.38	4.00	2	11
1.777	(1-12)	6	25.69	4.00	4	20
	(112)	6	25.69	4.00	4	20
1.715	(2-11)	6	26.69	0.00	4	0
	(211)	6	26.69	0.00	4	0

**Figure A.2** Data base of CuO to compare the  $d_{hkl}$ .

- The possible vectors are checked as shown in Figure A.3



**Figure A.3** Checked vectors for  $d_{hkl}$ .

$$\vec{r}_1 + \vec{r}_3 = \vec{r}_4$$

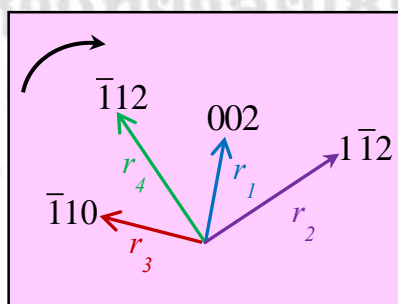
$$002 + \bar{1}10 = \bar{1}12$$

and

$$\vec{r}_1 + (-\vec{r}_3) = \vec{r}_2$$

$$002 + 1\bar{1}0 = 1\bar{1}2$$

- To find the direction of the electron beam incident by using right-hand rule of the cross vector, this is shown in Figure A.4. Any couple of vector is crossed in a clockwise direction and give same result of  $[uvw]$ .



**Figure A.4** Cross vectors for  $[uvw]$ .

$$\vec{r}_1 \times \vec{r}_2 \Rightarrow \begin{vmatrix} h & k & l \\ 0 & 0 & 2 \\ 1 & -1 & 2 \end{vmatrix} \Rightarrow [uvw] = [002]$$

$$\vec{r}_4 \times \vec{r}_1 \Rightarrow \begin{vmatrix} h & k & l \\ -1 & 1 & 2 \\ 0 & 0 & 2 \end{vmatrix} \Rightarrow [uvw] = [002]$$

$$\vec{r}_3 \times \vec{r}_4 \Rightarrow \begin{vmatrix} h & k & l \\ -1 & 1 & 0 \\ -1 & 1 & 2 \end{vmatrix} \Rightarrow [uvw] = [002]$$

$$\vec{r}_3 \times \vec{r}_1 \Rightarrow \begin{vmatrix} h & k & l \\ -1 & 1 & 0 \\ 0 & 0 & 2 \end{vmatrix} \Rightarrow [uvw] = [002]$$

Thus,  $[uvw] = [002]$ .

- To check for zone law this will present as, by follows;

$$hu + kv + lw = 0 \text{ (ZOLZ)} \quad (\text{A.2})$$

where  $hkl$  is the Miller indices for planes in crystal (Bravais) lattices, and  $uvw$  is the Miller indices for the direction of electron beam incident or zone axis.

$$\begin{aligned} (002) \cdot [uvw] &= (002) \cdot [220] = 0 \\ (1\bar{1}2) \cdot [uvw] &= (1\bar{1}2) \cdot [220] = 0 \\ (\bar{1}10) \cdot [uvw] &= (\bar{1}10) \cdot [220] = 0 \\ (\bar{1}12) \cdot [uvw] &= (\bar{1}12) \cdot [220] = 0 \end{aligned}$$

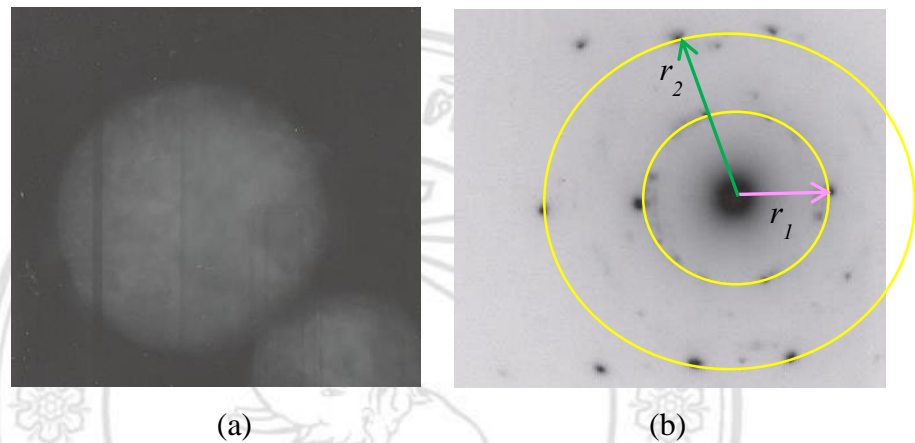
According to Equation (A.2),

The nanoparticle is a single crystal and its plans are 002,  $1\bar{1}2$ ,  $\bar{1}10$  and  $\bar{1}12$ , respectively. Moreover, the zone axis of the crystal is  $[002]$ . Therefore, the results correspond to the monoclinic structure of the CuO.

## 1.2 Cu<sub>2</sub>O nanoparticles

The diffraction pattern of some nanoparticles showed in ring pattern, which can be identified type and structure by camera constant methods as follows:

- To find radius, measure the distance from a spot center to the diffraction spots as shown in Figure A.5.



**Figure A.5** (a) TEM image of a copper oxide nanoparticle and (b) the diffraction pattern of the nanoparticle with  $r$ .

From the Figure A.5 (b),  $r_1 = 9 \text{ mm}$  and  $r_2 = 15 \text{ mm}$ .

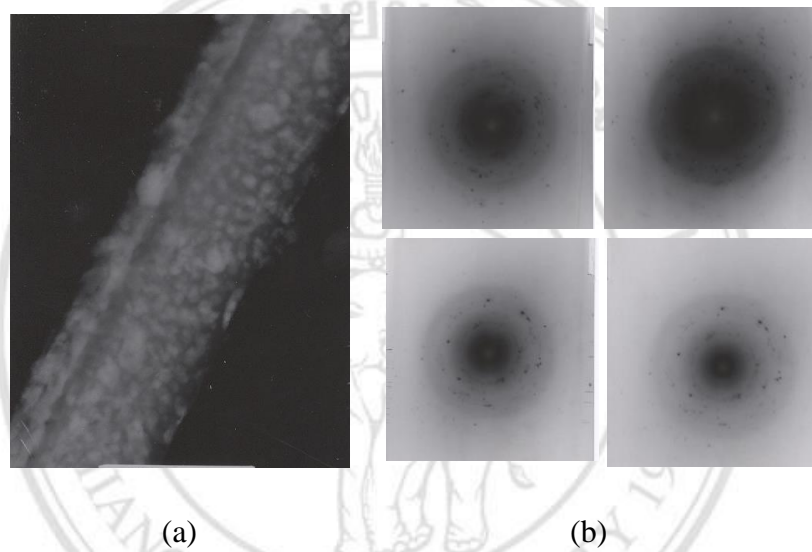
- Equation (A.1) is used to calculate  $d_{hkl}$ . Thus,

$$d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm} \text{ \AA}}{9 \text{ mm}} = 2.2503 \text{ \AA}$$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm} \text{ \AA}}{15 \text{ mm}} = 1.3502 \text{ \AA}$$

- Data base in program CaRIne v3.1 was used to compare  $d_1$  and  $d_2$ . From the data base, the results correspond to Cu<sub>2</sub>O structure.

## 2. The TEM Analysis of Copper Oxide Nanofibers



**Figure A.6** (a) A copper oxide nanofiber with white spots sticking on the fibers and (b) diffraction patterns of the white spots on the fiber.

The diffraction pattern of some spots sticking on the fibers showed in ring pattern, which can be identified type and structure by camera constant methods as follows:

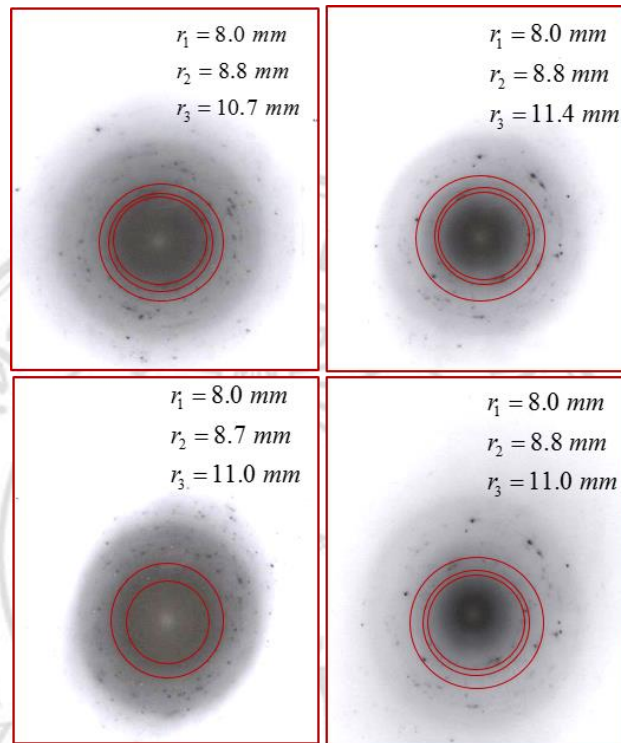
- To find radius, measure the distance from a spot center to the diffraction spots as shown in Figure A.7.
- Equation (A.1) is used to calculate  $d_{hkl}$ . Thus,

$$\text{Sample 1; } d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{\AA}}}{8.0 \text{ mm}} = 2.25316 \overset{\circ}{\text{\AA}}$$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{\AA}}}{8.8 \text{ mm}} = 2.3014 \overset{\circ}{\text{\AA}}$$



$$d_3 = \frac{L\lambda}{r_3} = \frac{20.2530 \text{ mm } \overset{\circ}{\text{Å}}}{10.7 \text{ mm}} = 1.8928 \overset{\circ}{\text{Å}}$$



**Figure A.7** Diffraction patterns of (a) the white spots in sample 1, (b) the white spots in sample 2, (c) the white spots in sample 3 and (d) the white spots in sample d.

Sample 2;  $d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm } \overset{\circ}{\text{Å}}}{8.0 \text{ mm}} = 2.25316 \overset{\circ}{\text{Å}}$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm } \overset{\circ}{\text{Å}}}{8.8 \text{ mm}} = 2.3014 \overset{\circ}{\text{Å}}$$

$$d_3 = \frac{L\lambda}{r_3} = \frac{20.2530 \text{ mm } \overset{\circ}{\text{Å}}}{11.4 \text{ mm}} = 1.7765 \overset{\circ}{\text{Å}}$$

Sample 3;  $d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm } \overset{\circ}{\text{Å}}}{8.0 \text{ mm}} = 2.25316 \overset{\circ}{\text{Å}}$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{Å}}}{8.7 \text{ mm}} = 2.3279 \overset{\circ}{\text{Å}}$$

$$d_3 = \frac{L\lambda}{r_3} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{Å}}}{11.0 \text{ mm}} = 1.8441 \overset{\circ}{\text{Å}}$$

Sample 4;  $d_1 = \frac{L\lambda}{r_1} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{Å}}}{8.0 \text{ mm}} = 2.25316 \overset{\circ}{\text{Å}}$

$$d_2 = \frac{L\lambda}{r_2} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{Å}}}{8.8 \text{ mm}} = 2.3014 \overset{\circ}{\text{Å}}$$

$$d_3 = \frac{L\lambda}{r_3} = \frac{20.2530 \text{ mm} \overset{\circ}{\text{Å}}}{11.0 \text{ mm}} = 1.8441 \overset{\circ}{\text{Å}}$$

Data base in program CaRIne v3.1 was used to compare  $d_1$  and  $d_2$ . From the data base,  $d_1, d_2$  and  $d_3$  of each sample are presented in Table A.1 It is clearly shown that the results correspond to CuO structure.

**Table A. 1** A comparison of the  $d_{hkl}$  from calculation with data base in program CaRIne v3.1.

Sample	Calculation of $d_{hkl}$	Data base of $d_{hkl}$			% error	
		CuO_Base center	Cu <sub>2</sub> O_Body center	Cu <sub>2</sub> O_Face center	CuO	Cu <sub>2</sub> O
1	2.5316	2.529	2.342	2.342	0.61	8.09
	2.3014	2.322	2.342	2.342	0.89	1.73
	1.8928	1.878	1.912	1.912	0.79	1.00
2	2.5316	2.529	2.342	2.342	0.61	8.09
	2.3014	2.322	2.342	2.342	0.89	1.73
	1.7765	1.776	1.656	1.656	0.03	7.28

3	2.5136	2.529	2.342	2.342	0.61	8.09
	2.3278	2.322	2.342	2.342	0.25	1.54
	1.8411	1.866	1.912	1.912	1.33	3.71
4	2.5316	2.529	2.342	2.342	0.61	8.09
	2.3014	2.322	2.342	2.342	0.89	1.73
	1.8411	1.866	1.912	1.912	1.33	3.71

## APPENDIX B

### Deriving physics equations

#### 1. The Penetration Depth of Conductor

As following Eq. (3.1) and Eq. (3.2),  $d = \frac{1}{\alpha}$ ,

where  $\alpha$  is the attenuation factor and can be represented as

$$\alpha = \omega \sqrt{\frac{\mu_0 \mu' \varepsilon_0 \varepsilon'}{2}} \sqrt{\left[1 + \left(\varepsilon''_{eff} / \varepsilon'\right)^2\right]^{1/2}} - 1.$$

For conductor being as high dielectric loss medium,  $\varepsilon''_{polarization} = 0, \varepsilon''_{eff} / \varepsilon' \gg 1$ .

Thus,

$$\begin{aligned}
\alpha &= \sqrt{\frac{\omega^2 \mu_0 \mu' \epsilon_0 \epsilon'}{2}} \sqrt{\left[ 1 + \left( \frac{\epsilon''_{eff}}{\epsilon'} \right)^2 \right]^{\frac{1}{2}} - 1} \\
&= \sqrt{\frac{\omega^2 \mu_0 \mu' \epsilon_0 \epsilon'}{2}} \sqrt{\left( \frac{\epsilon''_{eff}}{\epsilon'} \right)} \\
&= \sqrt{\frac{\omega^2 \mu_0 \mu' \epsilon_0 \epsilon' \epsilon''_{eff}}{2 \epsilon'}} \\
&= \sqrt{\frac{\omega^2 \mu_0 \mu' \epsilon_0 \epsilon''_{eff}}{2}}
\end{aligned}$$

Therefore,  $d = \frac{1}{\alpha} = \sqrt{\frac{\omega^2 \mu_0 \mu' \epsilon_0 \epsilon''_{eff}}{2}}$ .

Because  $\epsilon''_{eff}$  is the summation of losses from polarization and conduction,

$$\begin{aligned}
\epsilon''_{eff} &= \epsilon''_{polarization} + \epsilon''_{conduction} \\
&= \epsilon''_{polarization} + \frac{\sigma}{\omega \epsilon_0}
\end{aligned}$$

and for conductor  $\epsilon''_{polarization} = 0$ .

Thus,

$$\begin{aligned}
\epsilon''_{eff} &= \frac{\sigma}{\omega \epsilon_0} \\
\sigma &= \omega \epsilon_0 \epsilon''_{eff} \\
\sigma &= \frac{1}{\rho}
\end{aligned}$$

Therefore,

$$\begin{aligned}
d = \frac{1}{\alpha} &= \sqrt{\frac{2}{\omega^2 \mu_0 \mu' \varepsilon_0 \varepsilon_{\text{eff}}''}} \\
&= \sqrt{\frac{2}{\omega \mu_0 \mu' (\omega \varepsilon_0 \varepsilon_{\text{eff}}'' )}} \\
&= \sqrt{\frac{2}{\omega \mu_0 \mu' \sigma}} \\
&= \sqrt{\frac{2}{2\pi f \mu_0 \mu' \sigma}} \\
&= \sqrt{\frac{1}{\pi f \mu_0 \mu' \sigma}} \\
&= \sqrt{\frac{\rho}{\pi f \mu_0 \mu'}},
\end{aligned}$$

assume  $\mu' = 1$ ,

$$d = \sqrt{\frac{\rho}{\pi f \mu_0}} \quad \text{or} \quad d = \sqrt{\frac{1}{\sigma \pi f \mu_0}}.$$

## 2. Gibbs Equation with Nucleation

Following Gibbs equation in Eq. (3.8), at critical point  $(d\Delta G / dr) = 0$ , so

$$\frac{d}{dr} \Delta G = \frac{d}{dr} (4\pi r^2 \gamma) + \frac{d}{dr} \left( \frac{4}{3} \pi r^3 \Delta G_v \right)$$

$$0 = 8\pi r \gamma + 3 \left( \frac{4}{3} \right) \pi r^2 \Delta G_v$$

$$0 = 8\pi r \gamma + 4\pi r^2 \Delta G_v$$

$$-4\pi r^2 \Delta G_v = 8\pi r \gamma$$

$$-4\pi r^2 \Delta G_v = 8\pi r \gamma$$

$$-r \Delta G_v = 2\gamma$$

$$r = -\frac{2\gamma}{\Delta G_v}.$$

At critical radius,  $r = r_c$ , the total free energy of the system,  $\Delta G$ , is written as follows:

$$\begin{aligned}\Delta G &= 4\pi \left( -\frac{2\gamma}{\Delta G_v} \right)^2 \gamma + \frac{4}{3} \pi \Delta G_v \left( -\frac{2\gamma}{\Delta G_v} \right)^3 \\ &= \frac{16\pi\gamma^3}{\Delta G_v^2} - \frac{32\pi\gamma^3}{3\Delta G_v^2} \\ &= \frac{48 - 32}{3} \left( \frac{\pi\gamma^3}{\Delta G_v^2} \right) \\ &= \frac{16\pi\gamma^3}{3\Delta G_v^2}.\end{aligned}$$

Due to the total free energy of the system at the critical radius,  $r_c$ , shows the maximum energy barrier of height, so  $\Delta G = \Delta G^* = \frac{16\pi\gamma^3}{3\Delta G_v^2}$ .

However, free energy change per unit volume of solid from the liquid,  $\Delta G_v$ , depends on pressure of supersaturation,  $S$ , as shown in Eq. (3.10),

$$\Delta G_v = \frac{-k_B T}{\Omega} \ln(1+S).$$

Therefore,  $\Delta G^* = \frac{16\pi\gamma^3}{3\Delta \left( \frac{-k_B T}{\Omega} \ln(1+S) \right)^2}$  and this clearly shows that the maximum energy barrier,  $\Delta G^*$ , decreases with increasing of supersaturation,  $S$ .

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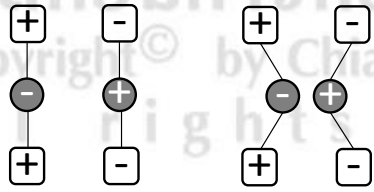
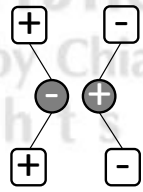
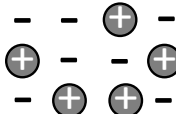
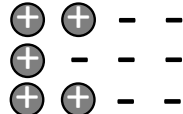
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## APPENDIX C

### The Physics Definition

#### 1. Polarization Mechanisms

**Table C.1** Mechanisms of different polarizations [91].

Kinds of polarization	No E field ( $E=0$ )	← Local E field ← ( $E \neq 0$ )	Mechanisms
Electronic			Electrons in an external electric field are shifted from equilibrium with respect to the positive nuclei and resulted in an induced dipole moment.
Orientation			The randomly oriented dipole moments respond to external electric field, try to align these asymmetric polar molecules leading to permanent dipoles parallel to the field.
Ionic			The positive and negative charges in crystals are displaced from their equilibrium position under external electric field resulting in the net dipole moment is non zero.
Interfacial			Under an external electric field, the more charges are displaced and accumulated at barrier resulting in interfacial polarization.



Polarization generally just means “orientation.” Polarization occurs from some kind of asymmetry in the interaction between spin and electromagnetic fields or matter. For electromagnetic waves, the vectors are the electric and magnetic fields, and the light’s polarization direction is by convention along the direction of the electric field. The illustrates of four kinds of polarization mechanism, electronic polarization, orientation polarization, ionic polarization, and interfacial polarization, and their mechanisms are shown in Table C.1.

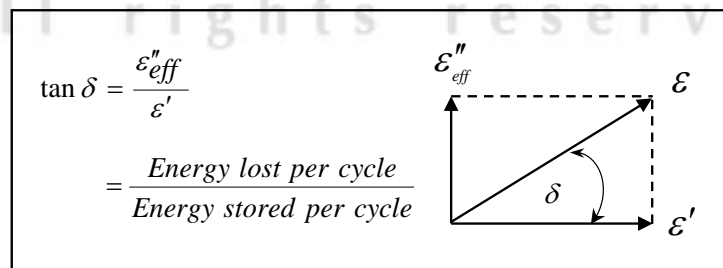
## 2. Dielectric loss

When an external electric field is applied to a dielectric material, some amount of electrical energy is absorbed by the dielectric material and is wasted in the form of heat. This loss is known as dielectric loss. A dielectric loss occurs from movement or rotation of atoms or molecules in an alternating electric field.

For microwave engineering, a loss material can be represented by relative dielectric constant,  $\epsilon'$ , and dissipation factor or loss tangent,  $\tan \delta$ , as the following equation [91]

$$\tan \delta = \frac{\epsilon''_{eff}}{\epsilon'}$$

where  $\delta$  is a phase lag, which occurred from dipolar reorientation of dielectric material in alternating electric field of microwave,  $\epsilon''_{eff}$  is the effective relative dielectric loss factor (a measure of the efficiency of converting microwave energy into heat), and  $\epsilon'$  is relative dielectric constant (a measure of polarization of a molecule in an electric field).



**Figure C.1** Loss tangent vector diagram.

The loss tangent vector diagram is shown in Figure C.1 ( $\mathcal{E}$  is relative permittivity). For very low loss materials, since  $\tan \delta \approx \delta$ , the loss tangent can be expressed in angle units, milliradians or microradians. Therefore, the loss power of microwave per surface area in a material due to dielectric loss,  $P_{dielectric\ loss}$ , as following [91]

$$P_{dielectric\ loss} = \omega \varepsilon_0 \varepsilon' \tan \delta |E_0|^2.$$



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- Publications**
1. K.Kaewyai, S. Choopun, M. Thepnurat, A.Gardchareon, S. Phadunghitidhada, , and D.Wongratanaphisan, "Preparation and characterization of copper oxide nanofibers by microwave-assisted thermal oxidation", Journal of Nanoelectronics and Optoelectronics 8 (2013) 472- 476.

2. K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadunghitidhada, and D. Wongratanaphisana, "Effects of mixed-phase copper oxide nanofibers in ZnO dye-sensitized solar cells on efficiency enhancement" , Journal of Nanoscience and Nanotechnology, Accepted status.
3. K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadunghitidhada, and D. Wongratanaphisana, "CuO-Cu<sub>2</sub>O nanocomposite layer for light-harvesting enhancement in ZnO dye-sensitized solar cells", Submitted to Materials Chemistry and Physics.
4. K. Kaewyai, S.Choopun, A. Gardchareon, P. Ruankham, S. Phadunghitidhada, and D. Wongratanaphisana, "Mechanism and experimental evidence of rapid morphological variant of copper oxide nanostructures by microwave heating", Submitted to Nanoscale.

#### Conferences

1. Karakade Kaewyai, Atcharawon Gardchareon, and Duangmanee Wongratanaphisan, "Synthesis and Characterization of Nanocopper Oxides", International Workshop on Conference of Physics and Material Engineering (2013).
2. Karakade Kaewyai, Atcharawon Gardchareon, Supab Choopun , Suurachet Phadunghitidhada, Meechai Thepnurat and Duangmanee Wongratanaphisan, "Preparation of Nanocopper Oxides by Microwave and Characterization", Collaborative Conference on 3D & Materials Research (2013).
3. Karakade Kaewyai, Supab Choopun, Atcharawon Gardchareon, Surachet Phadunghitidhada, and Duangmanee Wongratanaphisan, "Synthesis and Characterization of

Copper Oxide Nanofibers”, International Conference on Nano/Molecular Medicine and Engineering (2013).

4. Chawalit Bhoomanee, Karakade Kaewyai, Supab Choopun, Sutthipoj Sutthana, Sornchai Tananchai, and Duangmanee Wongratanaphisan, “Annealing Effect of AZO Multilayer Thin Films”, International Conference on Nano/Molecular Medicine and Engineering (2013).
5. K. Kaewyai, A. Gardchareon, S. Choopun, S. Phadunghitidhada, P. Ruankham and D. Wongratanaphisan, “Screening copper oxide nanofibers as a barrier in ZnO dye-sensitized solar cells for efficiency enhancement” Eighth International Conference on Molecular Electronics and Bioelectronics (2015).

**Seminar/ Experience/  
Training**

1. Graduate Students Seminar in Technical of Research Publication: Regulations on Graduate Education 2554, on 12<sup>th</sup> December, 2012, time 8.30 - 13.00, Chiang Mai University
2. Siam Physics Congress 2013, during 21<sup>st</sup>–23<sup>th</sup> March, 2013 at Chiangmai Grandview Convention Center, Chiang Mai
3. Nanoscience and Nanotechnology Annual Seminar 2012, on 2<sup>nd</sup> April, 2013, time 9.00-15.30, Chiang Mai University.
4. English Training by Language Institute: Funding from Department of Physics and Materials Science, during 1<sup>st</sup> – 24<sup>th</sup> April, 2013 at Language Institute, Chiang Mai University.

5. Training of Oral Presentation in English: Funding from Graduate School, during 9<sup>th</sup> – 11<sup>th</sup> September, 2013 at Graduate School, Chiang Mai University.



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